

Keiko Masumoto

List of Publications by Year in descending order

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docs citations

33
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156
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|--|-----|-----------|
| 1 | Characterization of Si-added aluminum oxide (AlSiO) films for power devices. Applied Surface Science, 2010, 256, 1803-1806. | 6.1 | 23 |
| 2 | Growth of Prismatic GaN Single Crystals with High Transparency on Small GaN Seed Crystals by Ca ²⁺ -Li-Added Na Flux Method. Applied Physics Express, 2012, 5, 025503. | 2.4 | 20 |
| 3 | 4H-SiC Homoepitaxial Growth on Substrate with Vicinal Off-Angle Lower than 1°. ECS Journal of Solid State Science and Technology, 2013, 2, N3012-N3017. | 1.8 | 16 |
| 4 | Growth of silicon carbide epitaxial layers on 150-mm-diameter wafers using a horizontal hot-wall chemical vapor deposition. Journal of Crystal Growth, 2013, 381, 139-143. | 1.5 | 13 |
| 5 | Influence of inserting AlN between AlSiON and 4H-SiC interface for the MIS structure. Applied Surface Science, 2011, 257, 8307-8310. | 6.1 | 11 |
| 6 | Effect of additives on liquid phase epitaxy growth of non-polar GaN single crystals using Na flux method. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 457-460. | 0.8 | 9 |
| 7 | Suppression of short step bunching generated on 4H-SiC Si-face substrates with vicinal off-angle. Journal of Crystal Growth, 2014, 401, 673-676. | 1.5 | 9 |
| 8 | The Effects of Ba-Additive on Growth of α -Plane GaN Single Crystals Using Na Flux Method. Japanese Journal of Applied Physics, 2012, 51, 040203. | 1.5 | 8 |
| 9 | Influence of Epi-Layer Growth Pits on SiC Device Characteristics. Materials Science Forum, 0, 821-823, 177-180. | 0.3 | 8 |
| 10 | The Growth of 3-Inch 4H-SiC Si-Face Epitaxial Wafer with Vicinal Off-Angle. Materials Science Forum, 0, 740-742, 193-196. | 0.3 | 7 |
| 11 | Suppression of 3C-Inclusion Formation during Growth of 4H-SiC Si-Face Homoepitaxial Layers with a 1° Off-Angle. Materials, 2014, 7, 7010-7021. | 2.9 | 7 |
| 12 | Homoepitaxial growth and investigation of stacking faults of 4H-SiC C-face epitaxial layers with a 1° off-angle. Japanese Journal of Applied Physics, 2015, 54, 04DP04. | 1.5 | 7 |
| 13 | Homo-Epitaxial Growth on 2° Off-Cut 4H-SiC(0001) Si-Face Substrates Using H ₂ -SiH ₄ -C ₃ H ₈ CVD System. Materials Science Forum, 2014, 778-780, 214-217. | 0.3 | 5 |
| 14 | Study of spiral growth on 4H-silicon carbide on-axis substrates. Journal of Crystal Growth, 2017, 475, 251-255. | 1.5 | 5 |
| 15 | Annealing effect on photoluminescence of Tb-doped AlBON films. Solid State Communications, 2010, 150, 1396-1399. | 1.9 | 4 |
| 16 | Luminescence Characteristics and Annealing Effect of Tb-Doped AlBNO Films for Inorganic Electroluminescence Devices. Japanese Journal of Applied Physics, 2011, 50, 04DH01. | 1.5 | 4 |
| 17 | Conversion of Basal Plane Dislocations to Threading Edge Dislocations in Growth of Epitaxial Layers on 4H-SiC Substrates with a Vicinal Off-Angle. Materials Science Forum, 0, 778-780, 99-102. | 0.3 | 4 |
| 18 | C-Face Epitaxial Growth of 4H-SiC on Quasi-150-mm Diameter Wafers with High Throughput. Materials Science Forum, 0, 778-780, 109-112. | 0.3 | 4 |

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 19 | Uniformity Improvement in Carrier Concentration on 150 mm Diameter C-Face Epitaxial Growth of 4H-SiC. Materials Science Forum, 2015, 821-823, 169-172. | 0.3 | 4 |
| 20 | Effect of nitrogen doping on the properties of AlSiO film for wide bandgap semiconductors. Applied Surface Science, 2010, 257, 1437-1440. | 6.1 | 3 |
| 21 | Luminescence Characteristics and Annealing Effect of Tb-Doped AlBNO Films for Inorganic Electroluminescence Devices. Japanese Journal of Applied Physics, 2011, 50, 04DH01. | 1.5 | 3 |
| 22 | The Effects of Substrate Surface Treatments on Growth of a -Plane GaN Single Crystals Using Na Flux Method. Japanese Journal of Applied Physics, 2012, 51, 035501. | 1.5 | 2 |
| 23 | Development of Homoepitaxial Growth Technique on 4H-SiC Vicinal Off Angled Substrate. Materials Science Forum, 2014, 778-780, 125-130. | 0.3 | 2 |
| 24 | Improvement of 4H-SiC Epitaxial Layers Grown on 2° Offcut Si-Face Substrates. Materials Science Forum, 0, 858, 133-136. | 0.3 | 2 |
| 25 | Investigation of Factors Influencing the Occurrence of 3C-Inclusions for the Thick Growth of on-Axis C-Face 4H-SiC Epitaxial Layers. Materials, 2020, 13, 4818. | 2.9 | 2 |
| 26 | Growth and properties of YAIO film synthesized by RF magnetron sputtering. Applied Surface Science, 2009, 255, 5021-5024. | 6.1 | 1 |
| 27 | Reducing the Wafer Off Angle for 4H-SiC Homoepitaxy. ECS Transactions, 2013, 58, 111-117. | 0.5 | 1 |
| 28 | Investigation of Low Off-Angled 4H-SiC Epitaxial Wafers for Power Device Applications. ECS Journal of Solid State Science and Technology, 2017, 6, P547-P552. | 1.8 | 1 |
| 29 | Reducing warpage of thick 4H-SiC epitaxial layers by grinding the back of the substrate. Japanese Journal of Applied Physics, 2019, 58, SBBD10. | 1.5 | 1 |
| 30 | Synthesis and Characterization of Tb-doped AlBNO Films for Electroluminescence Devices. Materials Research Society Symposia Proceedings, 2009, 1195, 295. | 0.1 | 0 |
| 31 | Characterization of Lanthanoid and Aluminum Based Oxide Film for Wide Bandgap Semiconductors. Materials Science Forum, 2010, 638-642, 3943-3948. | 0.3 | 0 |
| 32 | Dependence of the Growth Parameters on the In-Plane Distribution of 150 mm \uparrow Size SiC Epitaxial Wafer. Materials Science Forum, 2014, 778-780, 139-142. | 0.3 | 0 |